ON Semiconductor

Final Product/Process Change Notification

Document # : FPCN20828Z
Issue Date: 12 March 2015

Title of Change:	Change Lead frame N03503D003 to Lead frame N03503D005 For TSOP6 – NLVAS4599DTT1G.
Proposed first ship date:	12 March 2016
Contact information:	Contact your local ON Semiconductor Sales Office or <ricardo.avila@onsemi.com>
Samples:	Contact your local ON Semiconductor Sales Office
Additional Reliability Data:	Contact your local ON Semiconductor Sales Office or jose.aguilar@onsemi.com>.
Type of notification:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 12 months prior to implementation of the change. ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <PCN.Support@onsemi.com>.
Change Part Identification:	Date Code 2016, week 10 or later will contain this change.

Change category(s):

☐ Wafer Fab Change
☒ Assembly Change
☐ Test Change
☐ Manufacturing Site Change/Addition
☐ Manufacturing Process Change
☒ Material Change
☐ Product specific change
☐ Datasheet/Product Doc change
☐ Shipping/Packaging/Marking
☐ Other: _____

Sites Affected:	Site 1	Site 2
☐ All site(s) ☐ not applicable ☒ ON Semiconductor site(s) : ☐ External Foundry/Subcon site(s):	ON Seremban, Malaysia	

Description and Purpose:

ON Semiconductor is pleased to announce the introduction of a new lead frame for the products listed using the TSOP-6 Package Case Outline 318G-02.
The flag and Pin 3 are connected on this lead frame, setting the die bond pad, the substrate, flag and pin at the same potential (Gnd).
There are no changes to Electrical performance, Case outline or Foot print.

Reliability Data Summary:

#	Test	Name	Test Conditions	End Point Req's	Test Results (rej/ss)	
					Read Point	Lot A
1	PC	MSL1 preconditioning	3 IR @ 260 °C	c = 0, Room		all
2	TC-PC	Temperature Cycle	-65/+150 C	c = 0, Room	1000cyc	0/84
3	HAST-PC	Highly Accelerated Stress Test	Temp= +130°C, RH=85% , p = 18.8 psig, bias	c = 0, Room	96hrs	0/84
4	UHAST-PC	Unbiased Highly Accelerated Stress Test	Temp= +130°C, RH=85% , p = 18.8 psig, unbiased	c = 0, Room	96hrs	0/84

Based on the results presented here, device NLAS4599DTT1G housed in package TSOP6 with lead frame N03503D005, using technology TS60, assembled and tested at Seremban, Malaysia has met and exceeded the requirements and it is considered qualified per ON Semiconductor's Product Qualification Specifications, 12MSB17722C

Electrical Characteristic Summary:

Electrical Characteristics are not impacted

List of Affected Customer Specific Parts:

NLVAS4599DTT1G